

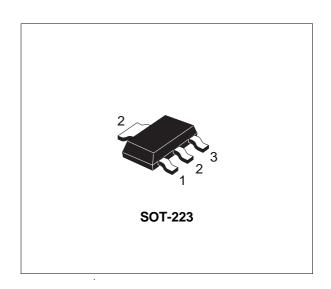
LOW POWER PNP TRANSISTOR

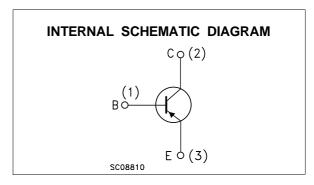
Ordering Code	Marking		
BCP52-16	BCP5216		

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BCP55-16

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I _E = 0)	-60	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	-60	V
V _{CER}	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-60	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V
Ic	Collector Current	-1	А
I _{CM}	Collector Peak Current (t _p < 5 ms)	-1.5	А
I_{B}	Base Current	-0.1	Α
I _{BM}	Base Peak Current (t _p < 5 ms)	-0.2	А
P _{tot}	Total Dissipation at T _{amb} = 25 °C	1.4	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	89.3	°C/W	ĺ
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Device mounted on a PCB area of 1 cm²

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

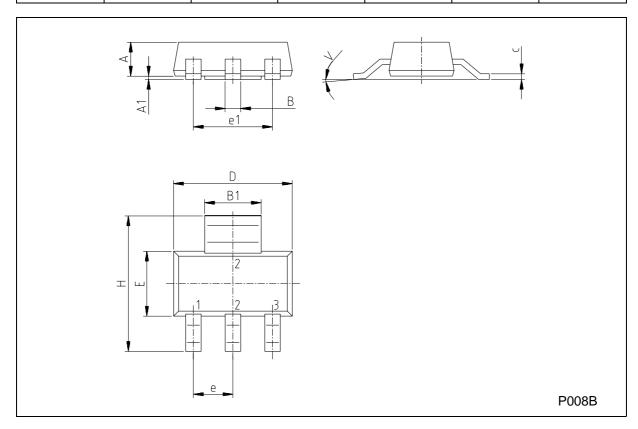
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	$V_{CB} = -30 \text{ V}$ $V_{CB} = -30 \text{ V}$ $T_j = 125 \text{ °C}$			-100 -10	nΑ μΑ
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA	-60			V
V _{(BR)CER}	Collector-Emitter Breakdown Voltage (R _{BE} = 1 KΩ)	I _C = -100 μA	-60			V
V _(BR) EBO	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = -500 \text{ mA}$ $I_B = -50 \text{ mA}$			-0.5	V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = -500 mA V _{CE} = -2 V			-1	V
h _{FE} *	DC Current Gain	I _C = -5 mA	40 100 25		250	
f _T	Transition Frequency	$I_{C} = -10 \text{ mA } V_{CE} = -5 \text{ V} f = 20 \text{ MHz}$		50		MHz

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1.5 %

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SOT-223 MECHANICAL DATA

DIM.	mm			inch		
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.80			0.071
В	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
С	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
е		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
Н	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



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